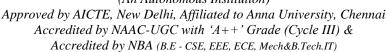


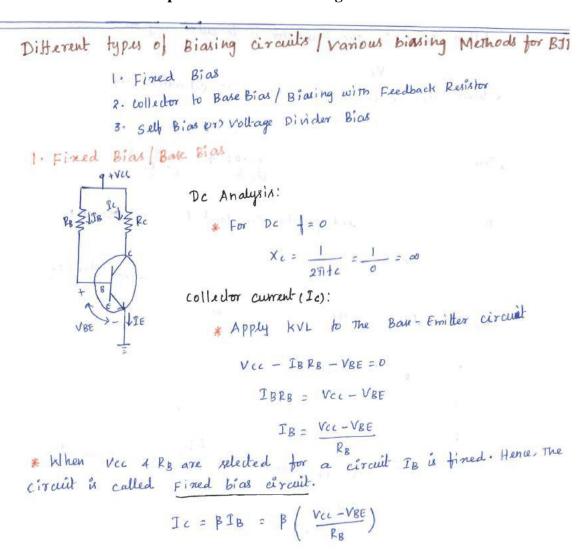
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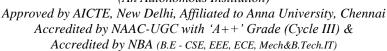
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**Topic 1.3: Fixed Bias configuration** 





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Collector Emitter Vollage (VCE)

\* Apply KVL to The collector - Emitter circuit

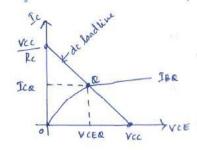
Load line Analysis

\* Apply KVI to the collector-Emilter circuit

\*This equ represents de load line with slope of - /pe 4 y-intercept

\* When Ic=0 ise The transistor is is cutoff region

VCE = 0 ie: the transistor is in contration region \* When



\* The saturation current for The circuit

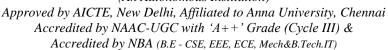
Stability factors

We Know That

No collector current present in This equation. So  $\frac{\partial S_B}{\partial I_C} = 0$  - (1)



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differentiate Ic with respect o Ic we get

$$\frac{\partial I_c}{\partial I_c} = \beta \frac{\partial I_B}{\partial I_c} + (1+\beta) \frac{\partial I_W}{\partial I_c} \qquad \frac{\partial I_C}{\partial I_{co}} = 5$$

$$1 = \beta \frac{\partial IB}{\partial Ic} + (1+\beta) \times \frac{1}{S}$$

$$1 - \beta \frac{\partial IB}{\partial Ic} = \frac{1 + \beta}{S}$$

$$S = \frac{1+\beta}{1-\beta \frac{\partial IB}{\partial Ie}} - \emptyset$$

\* Substitute 1 in 1

s':

$$S' = \frac{\partial Ic}{\partial V_{BE}} \Big| IEO + B constant (or) \frac{\Delta Ic}{\Delta V_{BE}} \Big| Ico + B constant$$

W. K. T

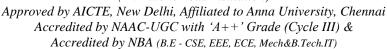
\* substitute IB in Ic

$$I_{\ell} = \frac{\beta V_{\ell \ell}}{R_B} - \frac{\beta V_B \epsilon}{R_B} + (1+\beta) I_{\ell D} - 3$$

\* differentiate w. r. to VBE



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Relation between 3 4 s

$$S = 1+B$$
  $ds' = \frac{-B}{RB}$  Absolute of  $M$  at all absolute  $M$ 

In s' Multiply neunerator 4 denominator by (1+B) we get

$$g' = -\frac{\beta(1+\beta)}{R_B(1+\beta)} = -\frac{\beta s}{R_B(1+\beta)}$$
 ...  $s = 1+\beta$ 

From 3
$$\exists c = \frac{\beta VCC}{RB} - \frac{\beta VBE}{PB} + (1+\beta) \Im CD$$

differentiate w.r. to 'B'

$$\frac{\partial Ic}{\partial \beta} = \frac{Vcc}{PB} - \frac{VBE}{PB} + I\omega$$

$$2 IB + Ico$$

$$= IB + 0$$

$$\frac{\partial Ic}{\partial B} = \frac{Ic}{B}$$

$$\frac{1}{B} = \frac{1}{B}$$

IB = VCC - VBE

$$S'' = \frac{\partial IL}{\partial \beta} = \frac{IC}{\beta}$$

Relation blw s 4 s"

$$S = 1+\beta$$
  $S^{11} = \frac{1c}{\beta}$ 

In s" Multiply Numerator 4 denominator by (1+B) we get

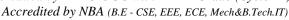
$$S^{11} = \frac{Ic(1+\beta)}{\beta(1+\beta)} = \frac{IcS}{\beta(1+\beta)}$$

Advantages:

- \* Simple circuit which use very few components.
- \* The operating point can be fined anywhere in The active region of The characteristics by simply changing the value of RB. Thus it provides manimum flenibility is the design.



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### Disadvantages

1. Thermal stability is not provided by this circuit - so the operation point is not maintained. Ic = BIB + ICEO

- 2. Since Ic= BIB 4 IB is already fined; Ic depends on B which change unit to unit 4 shifts me operating point.
- # The stabilization of operating point is very poor in The fined bias circuit. Because of this reason The fined bias circuit need some modifications.
  - # In The modified circuit, RB is connected blw collector 4 bak. Hence the circuit is called collector to bak bias circuit.